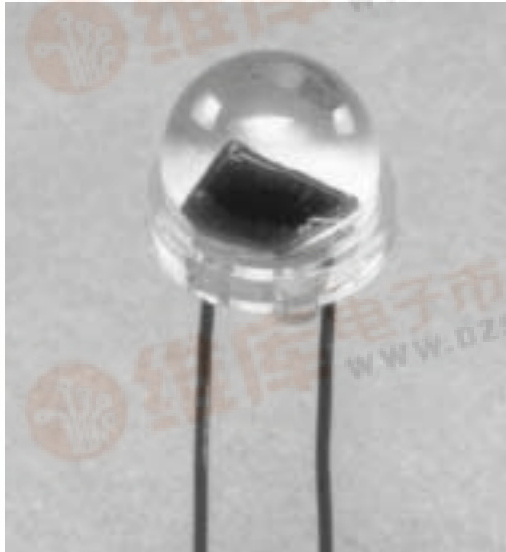
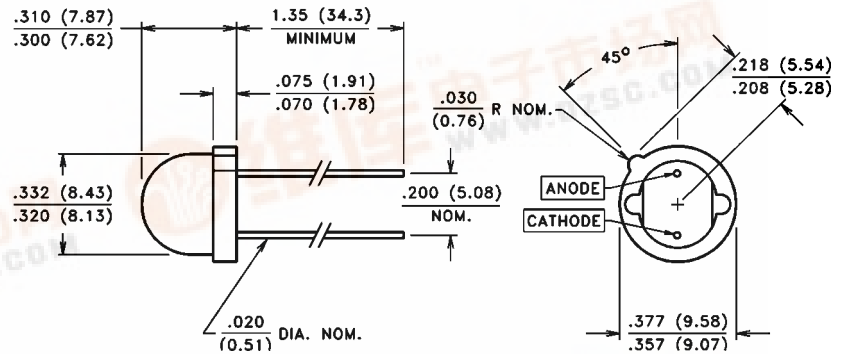


VTP Process Photodiodes

VTP1188S



PACKAGE DIMENSIONS inch (mm)



CASE 12 LENSED CERAMIC
CHIP ACTIVE AREA: .017 in² (1.1 mm²)

PRODUCT DESCRIPTION

Large area planar silicon photodiode mounted on a two lead ceramic substrate. A clear molded lens is used to increase sensitivity. Low junction capacitance permits fast response time.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C
Operating Temperature: -20°C to 75°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, page 46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP1188S			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K		200		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.20		%/°C
I _{SC}	Short Circuit Current	100 μW/cm ² , 880 nm	13		25	μA
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		.33		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 10 mV		3	30	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		67		GΩ
TC R _{SH}	R _{SH} Temperature Coefficient	H = 0, V = 10 mV		-11		%/°C
C _J	Junction Capacitance	H = 0, V = 0 V		.18	.30	nF
λ _{range}	Spectral Application Range		400		1100	nm
λ _p	Spectral Response - Peak			925		nm
S _R	Sensitivity	@ Peak		.55		A/W